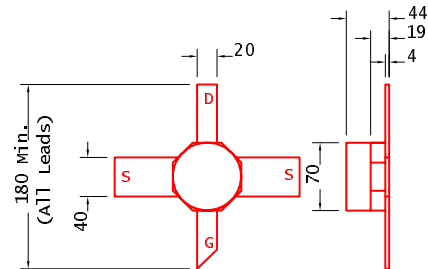


DATA SHEET
High Efficiency Heterojunction Power FET
Features

- **NON-HERMETIC LOW COST CERAMIC 70mil PACKAGE**
- **+26dBm TYPICAL OUTPUT POWER**
- **9.0dB TYPICAL POWER GAIN AT 12 GHZ**
- **0.4 dB TYPICAL NOISE FIGURE AT 2GHz**
- **20 dB TYPICAL ASSOCIATED GAIN AT 2 GHz**
- **0.3 X 600 MICRON RECESSED "MUSHROOM" GATE**
- **Si₃N₄ PASSIVATION**
- **ADVANCED EPITAXIAL HETEROJUNCTION PROFILE PROVIDES EXTRA HIGH POWER EFFICIENCY, AND HIGH RELIABILITY**

Applications

- **High Dynamic Range LNA**
- **DC to 18 GHz**



All Dimensions In mils.

ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

SYMBOLS	PARAMETERS/TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_{1dB}	Output Power at 1dB Compression V _{ds} =6V, I _{ds} =50% I _{ds} f=2GHz f=12GHz	24.0	26.0 25.5		dBm
G_{1dB}	Gain at 1dB Compression V _{ds} =6V, I _{ds} =50% I _{ds} f=2GHz f=12GHz	17.0 7.0	19.0 9.0		dB
PAE	Power Added Efficiency at 1dB Compression V _{ds} =6V, I _{ds} =50% I _{ds} f=2GHz f=12GHz		55 45		%
IP3	+5dBm P _{OUT} /Tone (5V/50mA) (5V/90mA) f=2GHz		28 31		dBm
NF	Noise Figure (5V/50mA) (5V/90mA) f=2GHz		0.4 0.6		dB
G_A	Associated Gain (5V/50mA) (5V/90mA) f=2GHz		20.0 20.0		dB
I_{ds}	Saturated Drain Current V _{ds} =3V, V _{gs} =0V	110	180	250	mA
G_m	Transconductance V _{ds} =3V, V _{gs} =0V	120	190		mS
V_p	Pinch-off Voltage V _{ds} =3V, I _{ds} =2.0mA		-1.0	-2.5	V
BV_{gd}	Drain Breakdown Voltage I _{gd} =1.0mA	-10	-15		V
BV_{gs}	Source Breakdown Voltage I _{gs} =1.0mA	-6	-14		V
R_{th}	Thermal Resistance		175*		°C/W

* Overall R_{th} depends on case mounting.

MAXIMUM RATINGS AT 25°C

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²
V_{ds}	Drain-Source Voltage	10V	6V
V_{gs}	Gate-Source Voltage	-6V	-3V
I_{ds}	Drain Current	I _{ds}	110mA
I_{gsf}	Forward Gate Current	30mA	5mA
P_{in}	Input Power	23dBm	@ 3dB Compression
T_{ch}	Channel Temperature	175°C	150°C
T_{stg}	Storage Temperature	-65/175°C	-65/150°C
P_t	Total Power Dissipation	780mW	650mW

Note: 1 Exceeding any of the above ratings may result in permanent damage.

2. Exceeding any of the above ratings may reduce MTTF below design goals.

Excelics Semiconductor, Inc., 2908 Scott Blvd., Santa Clara, CA 95054

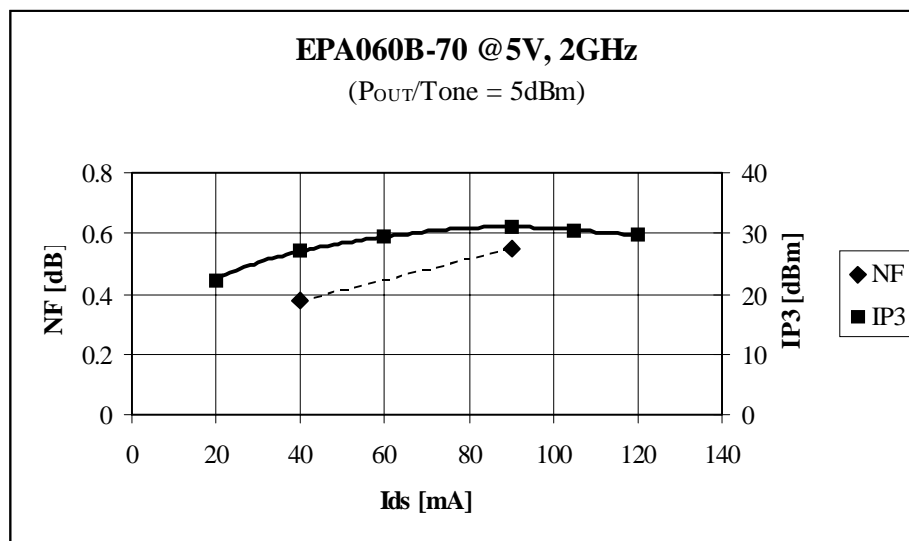
Phone: (408) 970-8664 Fax: (408) 970-8998 Web Site: www.excelics.com

DATA SHEET

High Efficiency Heterojunction Power FET

Typical Performance

Noise Figure & IP3



S-PARAMETERS

6V, 1/2 Idss								
FREQ	--- S11 ---		--- S21 ---		--- S12 ---		--- S22 ---	
(GHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1.0	0.863	-58.2	12.375	135.5	0.026	63.8	0.523	-24.4
2.0	0.696	-101.1	9.063	104.4	0.039	49.7	0.433	-41.0
3.0	0.604	-132.0	6.850	82.3	0.049	43.5	0.388	-51.9
4.0	0.555	-159.5	5.508	63.6	0.055	39.1	0.360	-60.8
5.0	0.538	177.3	4.614	47.0	0.065	35.5	0.322	-70.3
6.0	0.534	160.5	4.002	31.8	0.074	30.5	0.288	-84.5
7.0	0.533	141.8	3.532	16.7	0.083	25.3	0.281	-98.4
8.0	0.540	125.9	3.168	2.3	0.092	19.2	0.254	-111.5
9.0	0.582	105.0	2.817	-12.9	0.101	11.6	0.235	-125.6
10.0	0.622	88.1	2.532	-28.1	0.108	2.7	0.220	-148.1
11.0	0.642	74.5	2.370	-43.9	0.119	-8.1	0.225	-176.6
12.0	0.674	60.3	2.195	-60.1	0.129	-19.3	0.238	155.7
13.0	0.727	47.7	1.970	-74.8	0.132	-30.2	0.244	130.0
14.0	0.764	36.4	1.758	-88.3	0.133	-40.6	0.263	110.6
15.0	0.776	22.6	1.618	-104.8	0.137	-54.2	0.316	90.1
16.0	0.790	8.5	1.441	-122.5	0.134	-69.5	0.358	66.2
17.0	0.781	-1.1	1.285	-135.3	0.133	-78.3	0.363	51.0
18.0	0.792	-9.8	1.221	-147.7	0.144	-91.0	0.396	41.9
19.0	0.811	-22.2	1.106	-163.8	0.142	-106.2	0.418	23.9
20.0	0.836	-32.5	1.016	-179.0	0.144	-121.0	0.445	6.7
21.0	0.800	-41.8	0.975	166.9	0.157	-134.6	0.461	-8.4
22.0	0.761	-54.5	0.941	152.3	0.176	-148.9	0.426	-22.5
23.0	0.800	-68.3	0.861	134.7	0.190	-167.5	0.399	-50.3
24.0	0.799	-80.2	0.764	117.1	0.204	173.5	0.417	-78.5
25.0	0.719	-98.1	0.751	103.1	0.239	157.7	0.451	-87.9
26.0	0.718	-119.4	0.750	85.7	0.291	137.6	0.450	-110.4

EPA060B-70

DATA SHEET

High Efficiency Heterojunction Power FET

S-PARAMETERS

5V,50ma

FREQ (GHz)	--- S11 ---		--- S21 ---		--- S12 ---		--- S22 ---	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1.0	0.948	-57.7	14.366	129.2	0.032	54.0	0.439	-48.4
2.0	0.739	-100.4	9.162	106.8	0.042	45.1	0.438	-44.9
3.0	0.656	-132.4	7.008	84.9	0.050	36.7	0.392	-56.7
4.0	0.619	-155.0	5.629	67.5	0.056	31.8	0.352	-64.7
5.0	0.597	-176.9	4.740	51.0	0.062	26.9	0.298	-74.4
6.0	0.577	162.1	4.086	35.5	0.069	22.1	0.284	-90.6
7.0	0.580	141.7	3.546	21.4	0.075	18.2	0.287	-96.4
8.0	0.616	122.1	3.145	6.6	0.081	11.3	0.264	-103.5
9.0	0.618	117.3	2.918	-7.4	0.088	4.0	0.148	-131.4
10.0	0.633	99.5	2.657	-22.4	0.097	-1.1	0.185	-169.4
11.0	0.673	76.6	2.345	-36.9	0.101	-10.0	0.208	-168.3
12.0	0.718	63.1	2.142	-50.5	0.108	-18.0	0.156	179.2
13.0	0.761	59.0	1.999	-65.3	0.117	-27.9	0.223	117.8
14.0	0.777	44.3	1.767	-81.5	0.118	-40.9	0.321	97.0
15.0	0.779	30.7	1.543	-91.8	0.115	-46.4	0.287	96.4
16.0	0.816	14.8	1.418	-107.4	0.117	-59.0	0.265	77.7
17.0	0.827	11.9	1.307	-123.3	0.121	-70.7	0.445	49.2
18.0	0.822	2.7	1.114	-132.8	0.114	-77.5	0.460	49.8
19.0	0.852	-9.8	1.090	-144.6	0.123	-87.1	0.424	38.2
20.0	0.868	-19.9	1.001	-158.4	0.122	-99.4	0.442	21.5
21.0	0.846	-31.4	0.911	-174.9	0.120	-114.7	0.576	9.4
22.0	0.838	-32.7	0.856	176.8	0.125	-121.6	0.515	9.9
23.0	0.860	-47.9	0.832	160.7	0.130	-137.4	0.446	-22.9
24.0	0.835	-66.2	0.763	141.8	0.128	-156.0	0.536	-40.8
25.0	0.819	-80.1	0.710	126.8	0.130	-170.6	0.536	-41.4
26.0	0.868	-78.4	0.699	111.8	0.145	174.2	0.383	-78.0

EPA060B-70 Noise Parameters

Vds=5V, Ids=50mA

Freq. (GHz)	Gamma Opt		Nfmin (dB)	Rn/50
	(MAG)	(ANG)		
2	0.46	44	0.45	0.11
4	0.35	96	0.55	0.08
6	0.23	165	0.75	0.06
8	0.27	-145	0.92	0.08
10	0.35	-85	1.37	0.23
12	0.46	-58	1.47	0.44
14	0.58	-33	1.92	0.89
16	0.68	-6	2.47	1.3
18	0.63	7	3.03	1.78
20	0.68	33	3.24	1.87
22	0.63	50	3.43	1.81
24	0.67	92	3.65	1.56
26	0.72	120	3.86	1.16